

U.S. Department of Commerce, Patent and Trademark Office (PTO Form 1449 modified)		Docket No. YOR920030469US1	Serial No. 10/669,898
INFORMATION DISCLOSURE STATEMENT BY APPLICANT		Applicant Cabral, et al.	Confirmation No.:
(Use several sheets if necessary)		Filing Date 09/24/2003	Group 2924
Examiner			

U.S. Patent Documents

*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
	A1						
	A2						
	A3						
	A4						
	A5						
	A6						
	A7						
	A8						

Foreign Patent Documents

*Examiner Initial		Document Number	Date	Country	Class	Subclass	Translation	
							YES	NO
	B1						<input type="checkbox"/>	<input type="checkbox"/>
	B2						<input type="checkbox"/>	<input type="checkbox"/>
	B3						<input type="checkbox"/>	<input type="checkbox"/>
	B4						<input type="checkbox"/>	<input type="checkbox"/>

OTHER ART

*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.
OW	C1	Kedzierski, et al., "Metal-gate FinFET and fully-depleted SOI devices using total gate silicidation," International Electron Devices Meeting, Conference Digest, December 2002, Page(s): 247 -250
OW	C2	Krivokapic, et al., "Nickel Silicide Metal Gate FDSOI Devices with Improved Gate Oxide Leakage," IEDM 2002, pp. 271-274.
OW	C3	Maszara, et al., "Transistors with Dual Work Function Metal Gates by Single Full Silicidation (FUSI) of Polysilicon Gates," AMD 2002 Analyst Meeting, November 7, 2002
OW	C4	Qin, et al., "Investigation of Polycrystalline Nickel Silicide Films as a Gate Material," J. the Electrochemical Soc., 148(5), G271-G274, (2001)

Examiner Christa Wilson Date Considered 1/12/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.